

# BCV64B

# PNP general-purpose double transistor Rev. 4 — 2 August 2010

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

PNP general-purpose double transistor in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Package		PNP complement
	NXP	JEITA	
BCV64B	SOT143B	-	BCV63B

#### 1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V and 6 V)
- AEC-Q101 qualified
- Small SMD plastic package

#### 1.3 Applications

- General-purpose switching and amplification
- For use in Schmitt trigger applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
I <sub>C</sub>	collector current		-	-	-100	mΑ
Transisto	r TR1					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-30	V
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ mV};$ $I_C = -2 \text{ mA}$	220	-	475	
Transisto	r TR2					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-6	V
h <sub>FE</sub>	DC current gain	$V_{CE} = -700 \text{ V};$ $I_{C} = -2 \text{ mA}$	<u>[1]</u> 220	-	475	

<sup>[1]</sup> Due to matched dies,  $h_{\text{FE}}$  values for TR2 are the same as for TR1.



#### PNP general-purpose double transistor

# 2. Pinning information

Table 3. Pinning

Table 3.	Finning		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2 and base TR1		0 4
2	collector TR1	4 3	2 1
3	emitter TR1 and TR2		TR1
4	base TR2	1 2	TR2
			006aab230

# 3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BCV64B	-	plastic surface-mounted package; 4 leads	SOT143B		

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
BCV64B	*C6

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

#### PNP general-purpose double transistor

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	sistor				
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-200	mA
I <sub>B</sub>	base current		-	-100	mA
Transisto	or TR1				
$V_{CBO}$	collector-base voltage	open emitter	-	-30	V
$V_{CEO}$	collector-emitter voltage	open base	-	-30	V
Transisto	or TR2				
$V_{CBO}$	collector-base voltage	open emitter	-	-6	V
$V_{CEO}$	collector-emitter voltage	open base	-	-6	V
Per device	ce				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB).

#### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB.

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#### 7. Characteristics

Table 8. Characteristics

 $T_i = 25$  °C unless otherwise specified

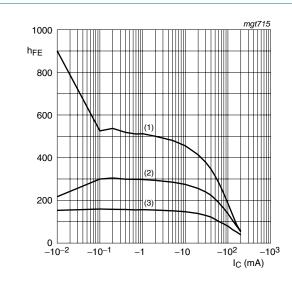
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I <sub>CBO</sub>	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$		-	-	<b>-5</b>	μА
$V_{CEsat}$	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$		-	<del>-</del> 75	-300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	[2]	-	-700	-	mV
Transisto	or TR1						
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$		220	-	475	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$		-	-250	-650	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	[2]	-	-850	-	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-600	-650	-750	mV
		$I_{C} = -10 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-	-	-820	mV
f⊤	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	4	-	pF
Transisto	or TR2						
h <sub>FE</sub>	DC current gain	$V_{CE} = -700 \text{ mV};$ $I_{C} = -2 \text{ mA}$	[1]	220	-	475	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$		-	-250	-	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CF} = -700 \text{ mV}$	[3]	-	-700	-	mV

<sup>[1]</sup> Due to matched dies,  $h_{\text{FE}}$  values for TR2 are the same as for TR1.

<sup>[2]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[3]</sup>  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

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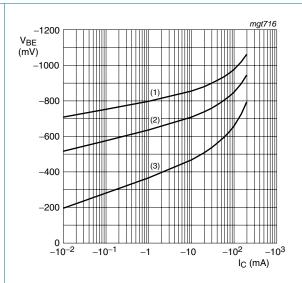
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 1. DC current gain as a function of collector current; typical values



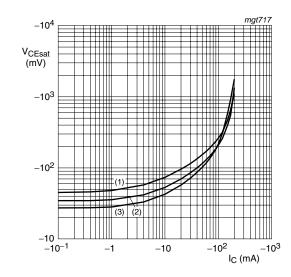
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 2. Base-emitter voltage as a function of collector current; typical values



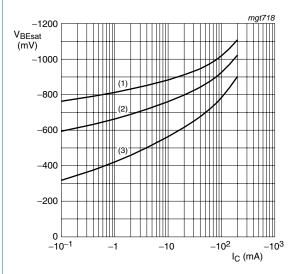
 $I_{\rm C}/I_{\rm B}=20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 3. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

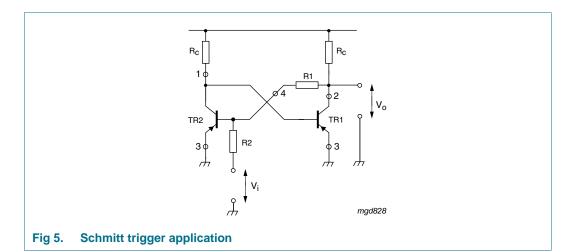
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

#### PNP general-purpose double transistor

# 8. Application information



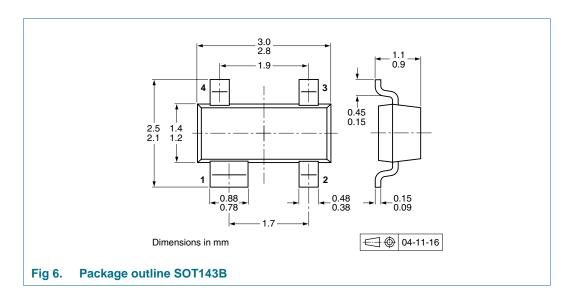
#### 9. Test information

#### 9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### PNP general-purpose double transistor

# 10. Package outline



# 11. Packing information

Table 9. Packing methods

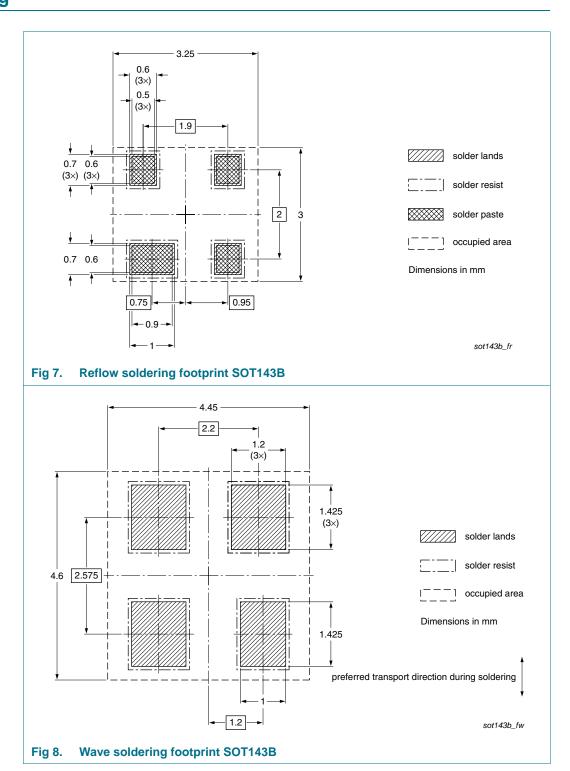
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BCV64B	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

<sup>[1]</sup> For further information and the availability of packing methods, see Section 15.

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### 12. Soldering





#### PNP general-purpose double transistor

# 13. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BCV64B v.4	20100802	Product data sheet	-	BCV64B_3			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	<ul> <li>Legal texts</li> </ul>	have been adapted to the n	ew company name whe	ere appropriate.			
	<ul> <li>Section 1 "I</li> </ul>	Product profile": amended.					
	<ul> <li>Section 3 "0</li> </ul>	Ordering information": added	d.				
	<ul> <li>Section 4 "I</li> </ul>	Marking": updated.					
	• <u>Figure 1, 2,</u>	3 and 4: added.					
	<ul> <li>Section 8 "/</li> </ul>	Application information": add	led.				
	Section 9 "Test information": added.						
	<ul> <li>Figure 6: superseded by minimized package outline drawing.</li> </ul>						
	Section 11	"Packing information": adde	d.				
	• Section 12	"Soldering": added.					
	Section 14	"Legal information": updated	d.				
BCV64B_3	19990521	Product specification	-	BCV64_CNV_2			
BCV64 CNV 2	19970310	Product specification	-	-			

#### PNP general-purpose double transistor

#### 14. Legal information

#### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### PNP general-purpose double transistor

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